

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of: **Toshihide KIKKAWA**

Serial Number: **Not Yet Assigned**

Filed: **March 31, 2004**

For: **COMPOUND SEMICONDUCTOR DEVICE AND METHOD OF  
FABRICATING THE SAME**

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

March 31, 2004

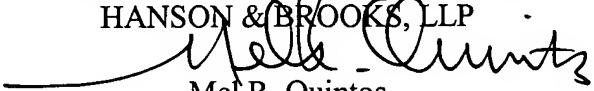
Sir:

In compliance with 37 CFR 1.56, Applicant calls to the attention of the Patent and  
Trademark Office the references listed on the attached PTO-1449.

A copy of each of the references is enclosed herewith.

In the event there are any fees due in connection with the filing of this paper, please  
charge Deposit Account No. 01-2340.

Respectfully submitted,  
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**23850**

PATENT TRADEMARK OFFICE

Enclosures: PTO-1449; References (3)

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 040153	Serial No. New Application
	Applicant(s): Toshihide KIKKAWA	
	Filing Date: March 31, 2004	Group Art Unit: Not Yet Assigned

#### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA AB					

#### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
_____	AC			
_____	AD			
_____	AE			
_____	AF			
_____	AG			

#### OTHER DOCUMENTS

_____	AH	Patent Abstracts of Japan, Publication Number 2001-185717, dated July 6, 2001.
_____	AI	Patent Abstracts of Japan, Publication Number 2002-359256, dated December 13, 2002.
_____	AJ	T. Hashizume, et al.; "Discrete surface state related to nitrogen-vacancy defect on plasma-treated GaN surfaces"; <i>Applied Physics Letters</i> ; Vol. 80; No. 24; June 17, 2002; pp. 4564-4566.

Examiner \_\_\_\_\_ Date Considered \_\_\_\_\_